

Vishay Semiconductors

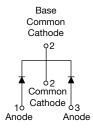
Ultrafast Rectifier, 16 A FRED Pt®

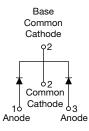




TO-263AB (D²PAK)

TO-262AA





VS-16CTU04SPbF

VS-16CTU04-1PbF

PRODUCT SUMMARY	
Package	TO-263AB (D ² PAK), TO-262AA
I _{F(AV)}	2 x 8 A
V_{R}	400 V
V _F at I _F	0.94 V
t _{rr} typ.	35 ns
T _J max.	175 °C
Diode variation	Common cathode

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

DESCRIPTION / APPLICATIONS

Vishay Semiconductors FRED Pt® series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V _{RRM}		400	V			
Average rectified forward current	I _{F(AV)}		8				
Average rectified forward current total device		Rated V _R , T _C = 155 °C	16				
Non-repetitive peak surge current	I _{FSM}	T _C = 25 °C	100	А			
Peak repetitive forward current	I _{FRM}	Rated V _R , square wave, 20 kHz, T _C = 155 °C	16				
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C			

ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	400	-	-		
Forward voltage	V _F	I _F = 8 A	-	- 1.19 1.3 V			
Forward voltage	VF	I _F = 8 A, T _J = 150 °C	-	0.94	1.0		
Devenue legicore essurant		$V_R = V_R$ rated	-	0.2	10		
Reverse leakage current	I _R	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	20	500	μA	
Junction capacitance	C _T	V _R = 400 V	-	14	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	



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DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, dI_F/dt =$	$I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{A}, V_R = 30 \text{ V}$		35	60	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	43	-	ns
		T _J = 125 °C	$I_F = 8 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	67	-	
Dools was assumed to the same of the same	I _{RRM}	T _J = 25 °C		-	2.8	-	A nC
Peak recovery current		T _J = 125 °C		-	6.3	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	60	-	
		T _J = 125 °C		-	210	-	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction to case per leg	R _{thJC}		-	1.8	2.0		
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	50	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-		
Maiabt			-	2.0	-	g	
Weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking daving		Case style TO-263AB (D2PAK)	16CTU04S				
Marking device		Case style TO-262		16CTU04-1			

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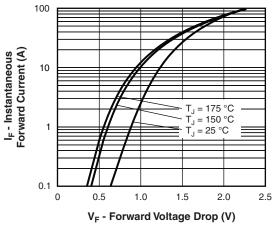


Fig. 1 - Typical Forward Voltage Drop Characteristics

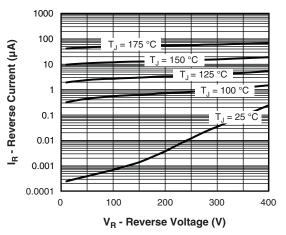


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

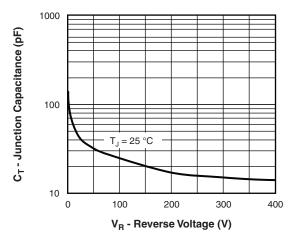


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

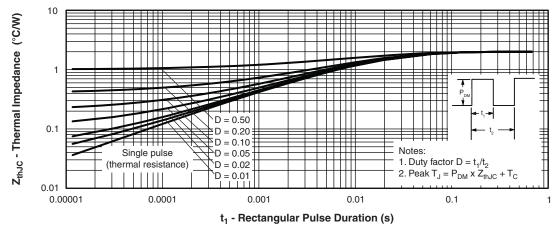


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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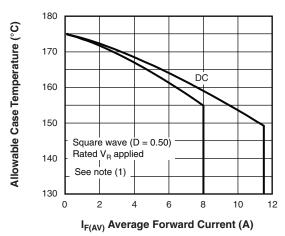


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

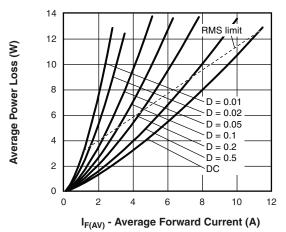


Fig. 6 - Forward Power Loss Characteristics

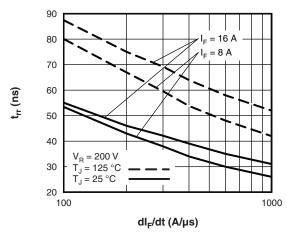


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

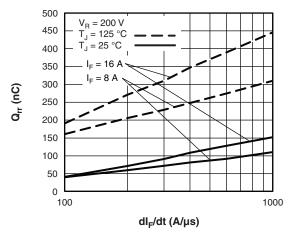


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{l} \text{(1)} \ \ \text{Formula used:} \ T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \ \text{at} \ (I_{F(AV)}/D) \ (\text{see fig. 6}); \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \ (1 - D); \ I_R \ \text{at} \ V_{R1} = \text{Rated} \ V_R \\ \end{array}$

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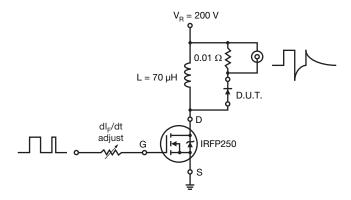
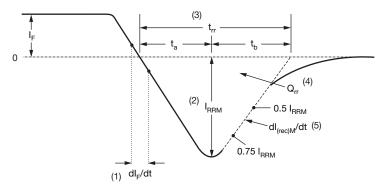


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dI_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

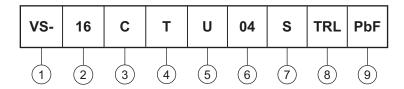
Fig. 10 - Reverse Recovery Waveform and Definitions

VS-16CTU04SPbF, VS-16CTU04-1PbF

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (16 A)

3 - C = common cathode

- T = TO-220, D²PAK

5 - U = ultrafast recovery

6 - Voltage rating (04 = 400 V)

7 - • S = D²PAK

• -1 = TO-262

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D²PAK package)

• TRR = tape and reel (right oriented, for D²PAK package)

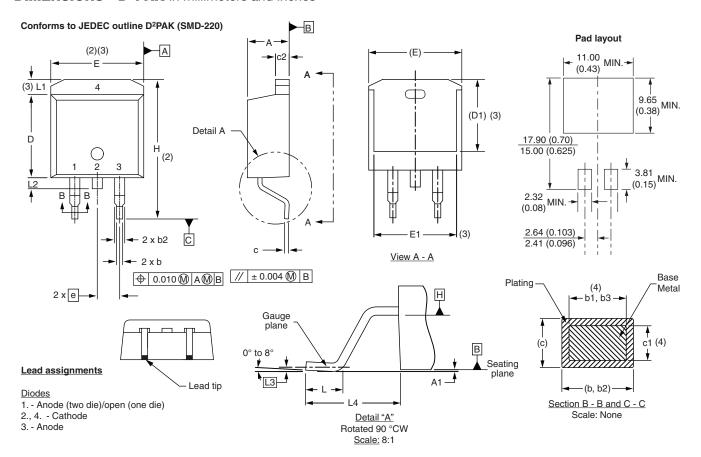
9 - PbF = lead (Pb)-free

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95014					
Part marking information	www.vishay.com/doc?95008					
Packaging information	www.vishay.com/doc?95032					

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D²**PAK**, **TO**-262

DIMENSIONS - D²PAK in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

Notes

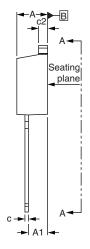
- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}$ Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch

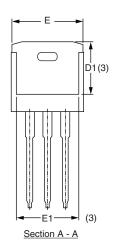
(7) Outline conforms to JEDEC outline TO-263AB

Document Number: 95014 Revision: 31-Mar-09



DIMENSIONS - TO-262 in millimeters and inches





⊕ 0.010 **M** A **M** B

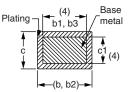
Lead assignments



--3 x b2 --3 x b

<u>Diodes</u>
1. - Anode (two die)/open (one die)
2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

SYMBOL	MILLIMETERS		INC	INCHES		
	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100) BSC		
L	13.46	14.10	0.530	0.555		
L1	-	1.65	-	0.065	3	
L2	3.56	3.71	0.140	0.146		

Notes

- $^{(1)}$ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline



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